SILVERMICRO

GK100PI60T6H

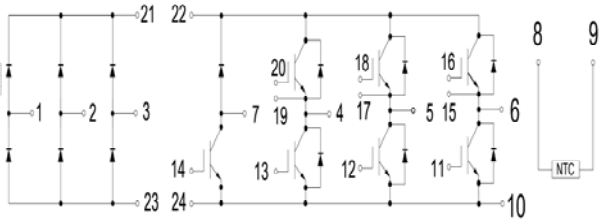
IGBT Module

Features：

- Short Circuit Rated 10μs
- Low Saturation Voltage: $V_{CE\ (sat)}$ = 1.80V @ I_C = 100A ,T_C=25℃
- 100% RBSOA Tested（2×Ic）
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement

Applications：

- Industrial Inverters



IGBT, Inverter

Maximum Rated Values (T_C=25℃Unless otherwise specified)

V_{CES}	Collector-Emitter Blocking Voltage		600	V
V_{GES}	Gate-Emitter Voltage		±20	V
I_C	Continuous Collector Current	T_C = 80℃,	100	A
		T_C = 25℃	175	A
I_{CM}	Repetitive Peak Collector Current	T_J = 150℃	200	A
t_{SC}	Short Circuit Withstand Time		>10	μs
P_D	Maximum Power Dissipation per IGBT	T_C = 25℃ T_{Jmax}=150℃	400	W

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Electrical Characteristics of IGBT (T_C=25℃Unless otherwise specified)

Static characteristics

Symbol	Description	Conditions		Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	I_C = 1 mA, V_{CE} = V_{GE}		4.0	4.7	5.5	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C = 100 A, V_{GE} = 15V	T_J = 25℃		1.80	2.00	V
			T_J = 125℃		2.10		V
I_{CES}	Collector-Emitter Leakage Current	V_{GE} = 0V, V_{CE} = V_{CES}, T_J = 25℃				1	mA
I_{GES}	Gate-Emitter Leakage Current	V_{GE} = ±20V, V_{CE} = 0V, T_J = 25℃				200	nA
C_{ies}	Input Capacitance	V_{CE} = 25V, V_{GE} = 0V , f =1MHz			6.30		nF
C_{oes}	Output Capacitance				0.58		nF

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	V_{CC} = 300V,I_C = 100A, R_G = 15 Ω,V_{GE} = ±15V, Inductive Load	T_J = 25℃		175		ns
			T_J = 125℃		175		
t_r	Rise Time		T_J = 25℃		130		ns
			T_J = 125℃		125		
$t_{d(off)}$	Turn-off Delay Time		T_J = 25℃		435		ns
			T_J = 125℃		445		
t_f	Fall Time		T_J = 25℃		125		ns
			T_J = 125℃		135		
E_{on}	Turn-on Switching Loss		T_J = 25℃		1.3		mJ
			T_J = 125℃		1.7		
E_{off}	Turn-off Switching Loss		T_J = 25℃		2.4		mJ
			T_J = 125℃		2.9		
Q_g	Total Gate Charge		T_J = 25℃		535		nC
RBSOA	Reverse Bias Safe Operation Area	I_C=200A,V_{CC}=480V,Vp=600V, Rg = 4.7Ω, V_{GE}=+15V to 0V, T_J =150°C		Trapezoid			
SCSOA	Short Circuit Safe Operation Area	V_{CC} = 300V, V_{GE} = 15V, T_J = 150℃		10			μs
$R_{\theta JC}$	IGBT Thermal Resistance: Junction-To-Case				0.31		℃/W

Diode, Inverter

Maximum Rated Values (T_C=25℃Unless otherwise specified)

V_{RRM}	Repetitive Peak Reverse Voltage	600	V
I_F	Diode Continuous Forward Current	100	A
I_{FM}	Diode Maximum Forward Current	200	A

Electrical Characteristics of FWD (T_C=25℃Unless otherwise specified)

Symbol	Description	Conditions		Min	Typ	Max	Unit
V_{FM}	Forward Voltage	I_F = 100 A , V_{GE} = 0V	T_J = 25℃		1.5		V
			T_J = 125℃		1.5		
I_{rr}	Peak Reverse Recovery Current	I_F=100A, di/dt =1400A/μs, V_{rr} = 300V, V_{GE} = -15V	T_J = 25℃		30		A
			T_J = 125℃		45		
Q_{rr}	Reverse Recovery Charge		T_J = 25℃		1.4		μC
			T_J = 125℃		3.5		
E_{rec}	Reverse Recovery Energy		T_J = 25℃		0.14		mJ
			T_J = 125℃		0.70		
$R_{\theta JC}$	Diode Thermal Resistance: Junction-To-Case				1.06		℃/W

IGBT, Brake-Chopper

Maximum Rated Values (T_C=25℃Unless otherwise specified)

V_{CES}	Collector-Emitter Blocking Voltage		600	V
V_{GES}	Gate-Emitter Voltage		±20	V
I_C	Continuous Collector Current	T_C = 80℃,	50	A
		T_C = 25℃	100	A
I_{CM}	Peak Collector Current Repetitive	T_J = 150℃	100	A
t_{SC}	Short Circuit Withstand Time		>10	μs
P_D	Maximum Power Dissipation per IGBT	T_C = 25℃ T_{Jmax}=150℃	265	W

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Electrical Characteristics of IGBT (T_C=25℃Unless otherwise specified)

Static characteristics

Symbol	Description	Conditions		Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	I_C = 1 mA, V_{CE} = V_{GE}		4.0	4.7	5.5	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C = 50 A, V_{GE} = 15V	T_J = 25℃		1.80	2.10	V
			T_J = 125℃		2.10		V
I_{CES}	Collector-Emitter Leakage Current	V_{GE} = 0V, V_{CE} = V_{CES}, T_J = 25℃				1	mA
I_{GES}	Gate-Emitter Leakage Current	V_{GE} = ±20V, V_{CE} = 0V, T_J = 25℃				200	nA
C_{ies}	Input Capacitance	V_{CE} = 25V, V_{GE} = 0V , f =1MHz			3.0		nF
C_{oes}	Output Capacitance				0.3		nF

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	V_{CC} = 300V,I_C = 50A, R_G =20Ω,V_{GE} = ±15V, Inductive Load	T_J = 25℃		90		ns
			T_J = 125℃		85		
t_r	Rise Time		T_J = 25℃		70		ns
			T_J = 125℃		70		
$t_{d(off)}$	Turn-off Delay Time		T_J = 25℃		190		ns
			T_J = 125℃		200		
t_f	Fall Time		T_J = 25℃		90		ns
			T_J = 125℃		110		
E_{on}	Turn-on Switching Loss		T_J = 25℃		0.4		mJ
			T_J = 125℃		0.8		
E_{off}	Turn-off Switching Loss		T_J = 25℃		0.7		mJ
			T_J = 125℃		1.1		
Q_g	Total Gate Charge		T_J = 25℃		260		nC
RBSOA	Reverse Bias Safe Operation Area	I_C=100A,V_{CC}=480V,Vp=600V, Rg = 20Ω, V_{GE}=+15V to 0V, T_J =150°C		Trapezoid			
SCSOA	Short Circuit Safe Operation Area	V_{CC} = 300V, V_{GE} = 15V, T_J = 150℃		10			μs
$R_{\theta JC}$	IGBT Thermal Resistance: Junction-To-Case				0.47		℃/W

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Diode, Brake-Chopper

Maximum Rated Values (T_C=25℃Unless otherwise specified)

V_{RRM}	Repetitive Peak Reverse Voltage	600	V
I_F	Diode Continuous Forward Current	50	A
I_{FM}	Diode Maximum Forward Current	100	A

Electrical Characteristics of FWD (T_C=25℃Unless otherwise specified)

Symbol	Description	Conditions		Min	Typ	Max	Unit
V_{FM}	Forward Voltage	I_F = 50 A , V_{GE} = 0V	T_J = 25℃		1.3		V
			T_J = 125℃		1.2		
I_{rr}	Peak Reverse Recovery Current	I_F = 50A, di/dt =1050A/μs, V_{rr} = 300V, V_{GE} = -15V	T_J = 25℃		30		A
			T_J = 125℃		40		
Q_{rr}	Reverse Recovery Charge		T_J = 25℃		2.4		μC
			T_J = 125℃		3.6		
E_{rec}	Reverse Recovery Energy		T_J = 25℃		0.25		mJ
			T_J = 125℃		0.65		
$R_{\theta JC}$	Diode Thermal Resistance: Junction-To-Case				1.37		℃/W

Diode, Rectifier (T_C=25℃Unless otherwise specified)

V_{RRM}	Repetitive Peak Reverse Voltage	T_J =25℃	1200	V
I_{FRMSM}	Maximum RMS Forward Current per Chip	T_J =80℃	100	A
I_{RMSM}	Maximum RMS Current at Rectifier Output	T_J =80℃	100	A
I_{FSM}	Surge Current @t_p=10 ms	T_J =25℃	800	A
		T_J =150℃	600	
I^2t	I²t - value	T_J =25℃	2760	A^2s
		T_J =150℃	1750	

Electrical Characteristics of Diode (T_C=25℃Unless otherwise specified)

Symbol	Description	Conditions		Min	Typ	Max	Unit
V_F	Forward voltage	I_F = 100 A ,	T_J =25℃		1.20	1.30	V
			T_J =125℃		1.15		
I_R	Reverse current	V_R=1200V	T_J =25℃			1	mA
$R_{\theta JC}$	Diode Thermal Resistance: Junction-To-Case				0.45		℃/W

Internal NTC-Thermistor Characteristic

R_{25}	T_C =25℃	5		kΩ
△R/R	T_C =100℃， R_{100} =481Ω		±5	%
P_{25}	T_C =25℃	50		mW
$B_{25/50}$	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15K))]$	3380		K
$B_{25/80}$	$R_2=R_{25}\exp[B_{25/80}(1/T_2-1/(298.15K))]$	3440		K

Module

Symbol	Description		Min	Typ	Max	Unit
V_{iso}	Isolation Voltage(All Terminals Shorted)	f = 50Hz, 1minute	2500			V
T_J	Maximum Junction Temperature				150	℃
T_{JOP}	Maximum Operating Junction Temperature Range		-40		+150	℃
T_{stg}	Storage Temperature		-40		+125	℃
$R_{\theta CS}$	Case-To-Sink (Conductive Grease Applied)			0.1		℃/W
T	Mounting Screw:M5		4.0		6.0	N·m
G	Weight			300		g

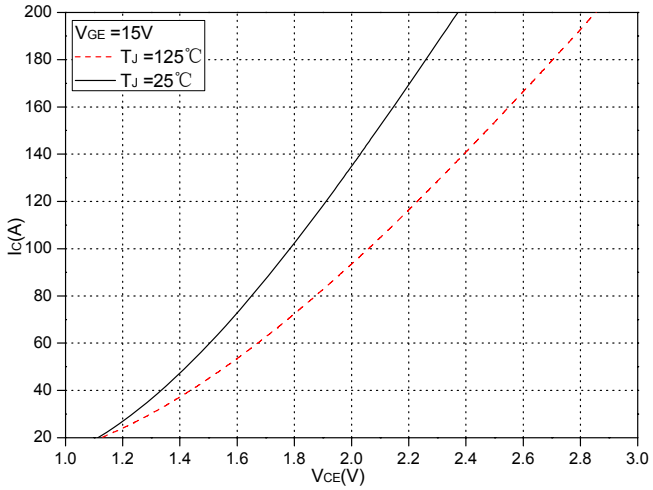


Fig.1 Typical Saturation Voltage Characteristics (Inverter)

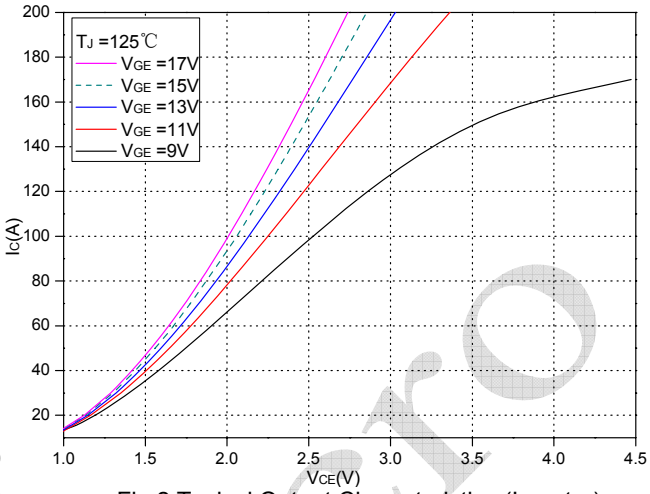


Fig.2 Typical Output Characteristics (Inverter)

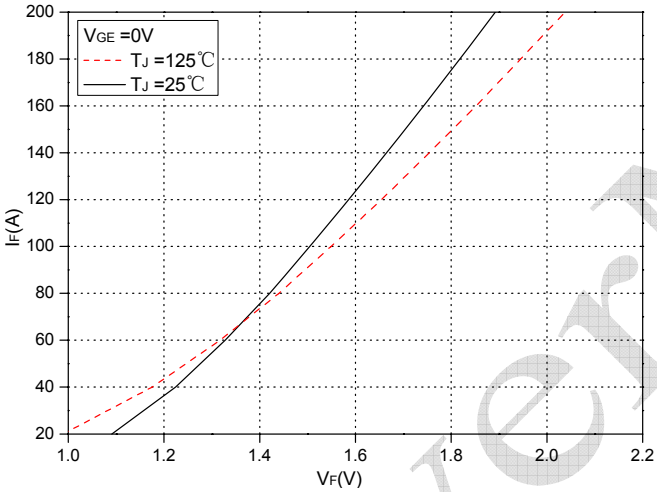


Fig.3 Forward Characteristics of FWD (Inverter)

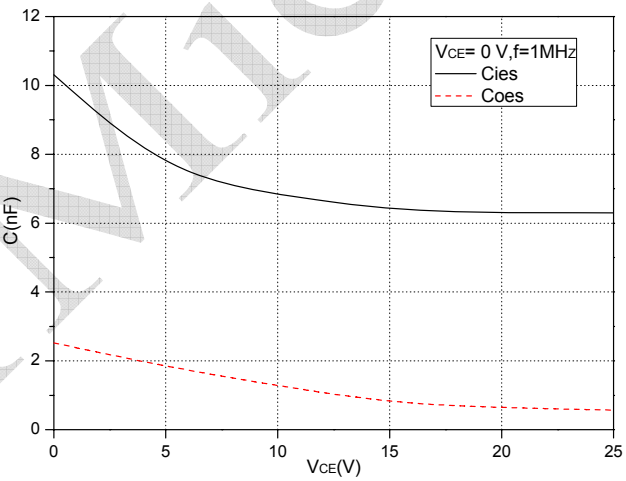


Fig.4 Capacitance Characteristics

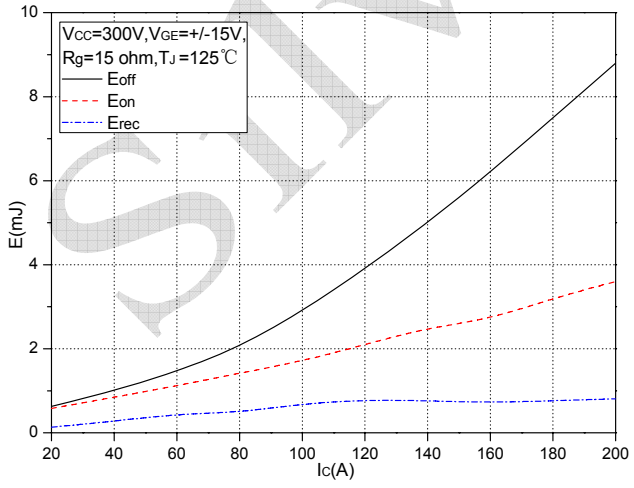


Fig.5 Typical Switching Loss vs. Collector Current (Inverter)

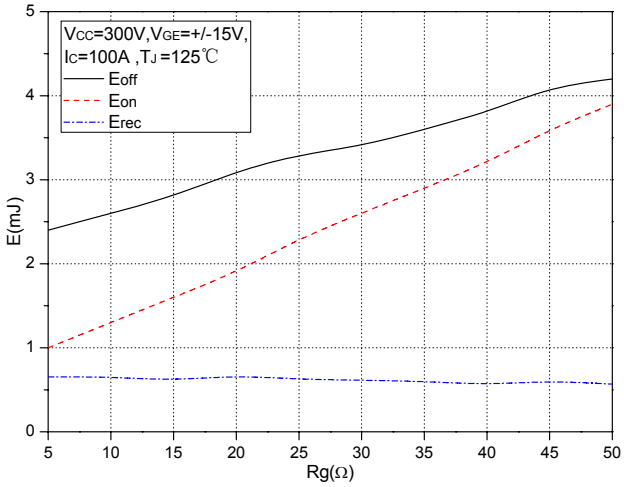


Fig.6 Typical Switching Loss vs. Gate Resistance (Inverter)

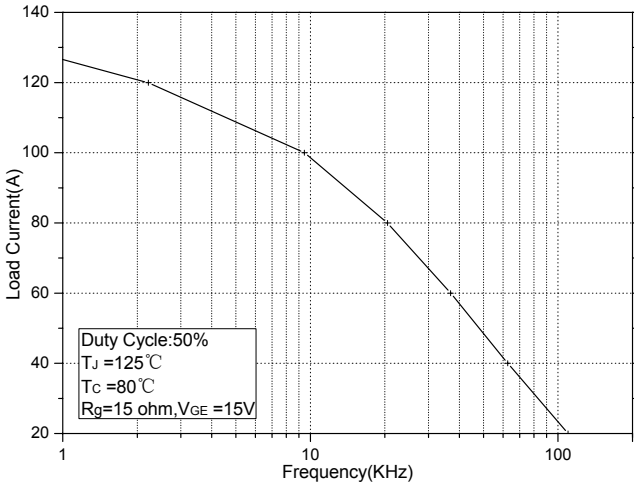


Fig.7 Typical Load Current vs. Frequency (Inverter)

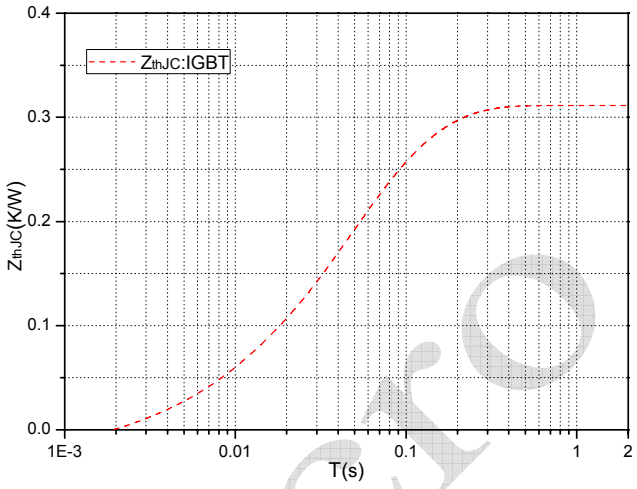


Fig.8 Transient Thermal Impedance IGBT (Inverter)

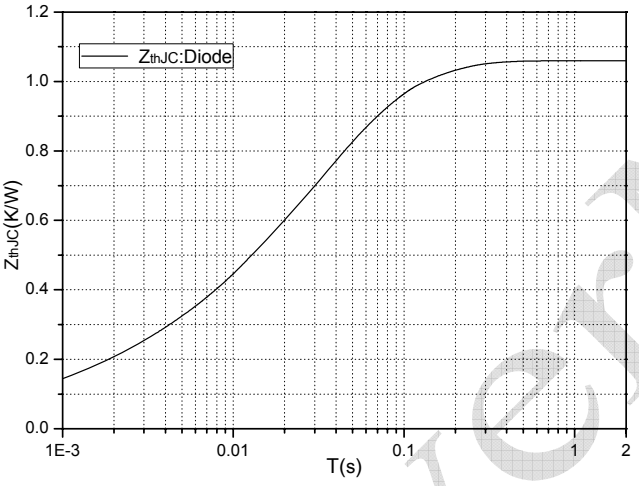


Fig.9 Transient thermal impedance Diode (Inverter)

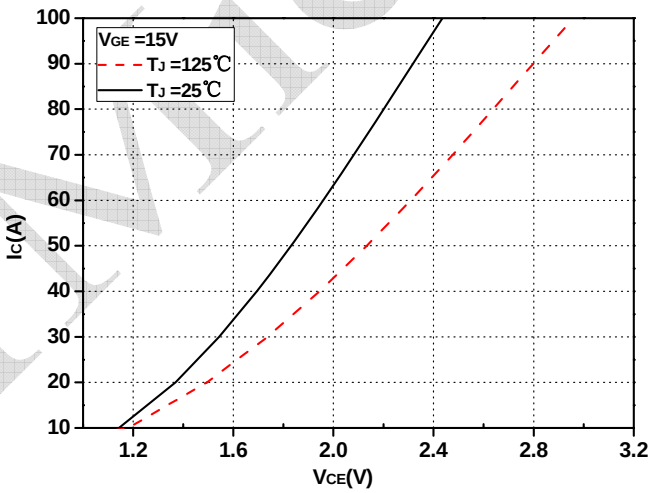


Fig.10 Typical Saturation Voltage Characteristics (Brake-Chopper)

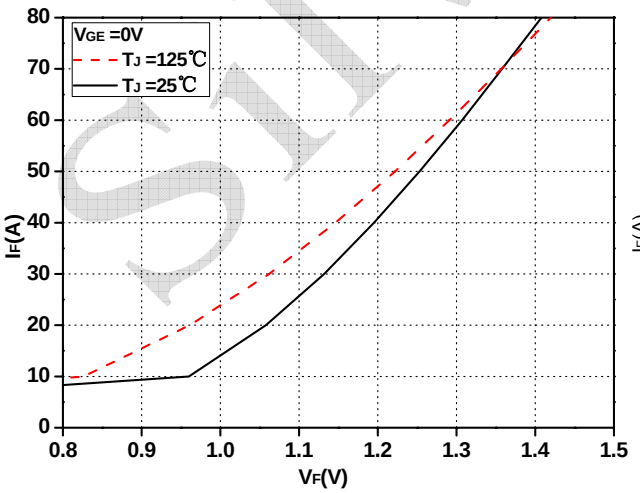


Fig.11 Forward Characteristics of FWD (Brake-Chopper)

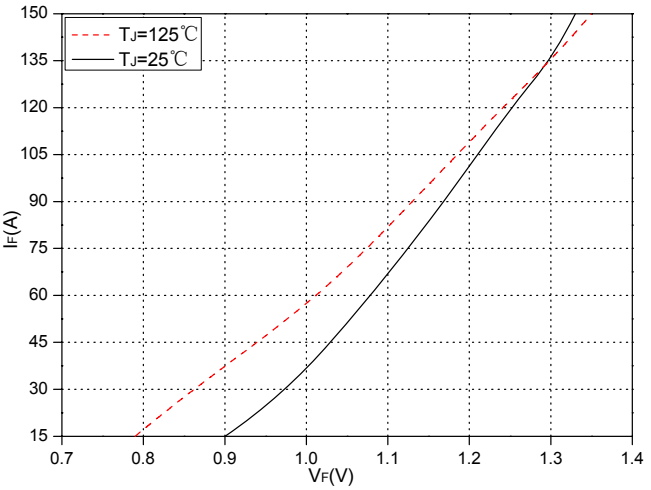


Fig.12 Forward Characteristics of Diode (Rectifier)

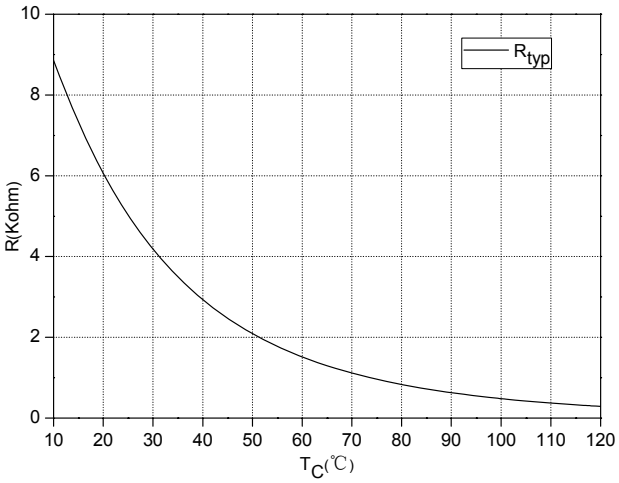


Fig.13 NTC Temperature characteristics

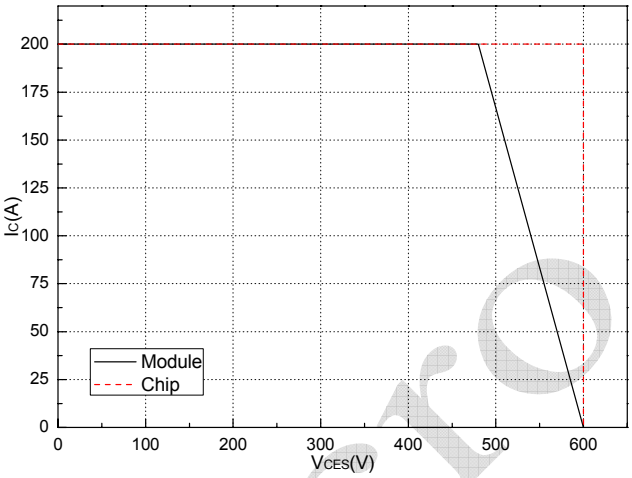
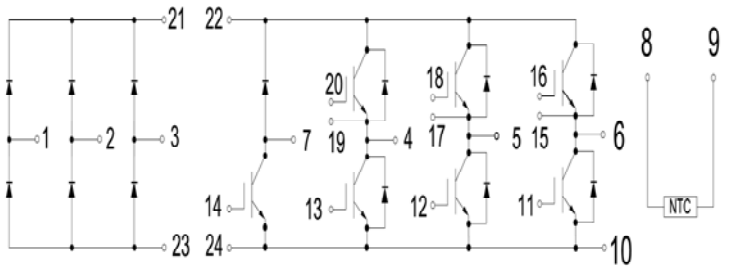
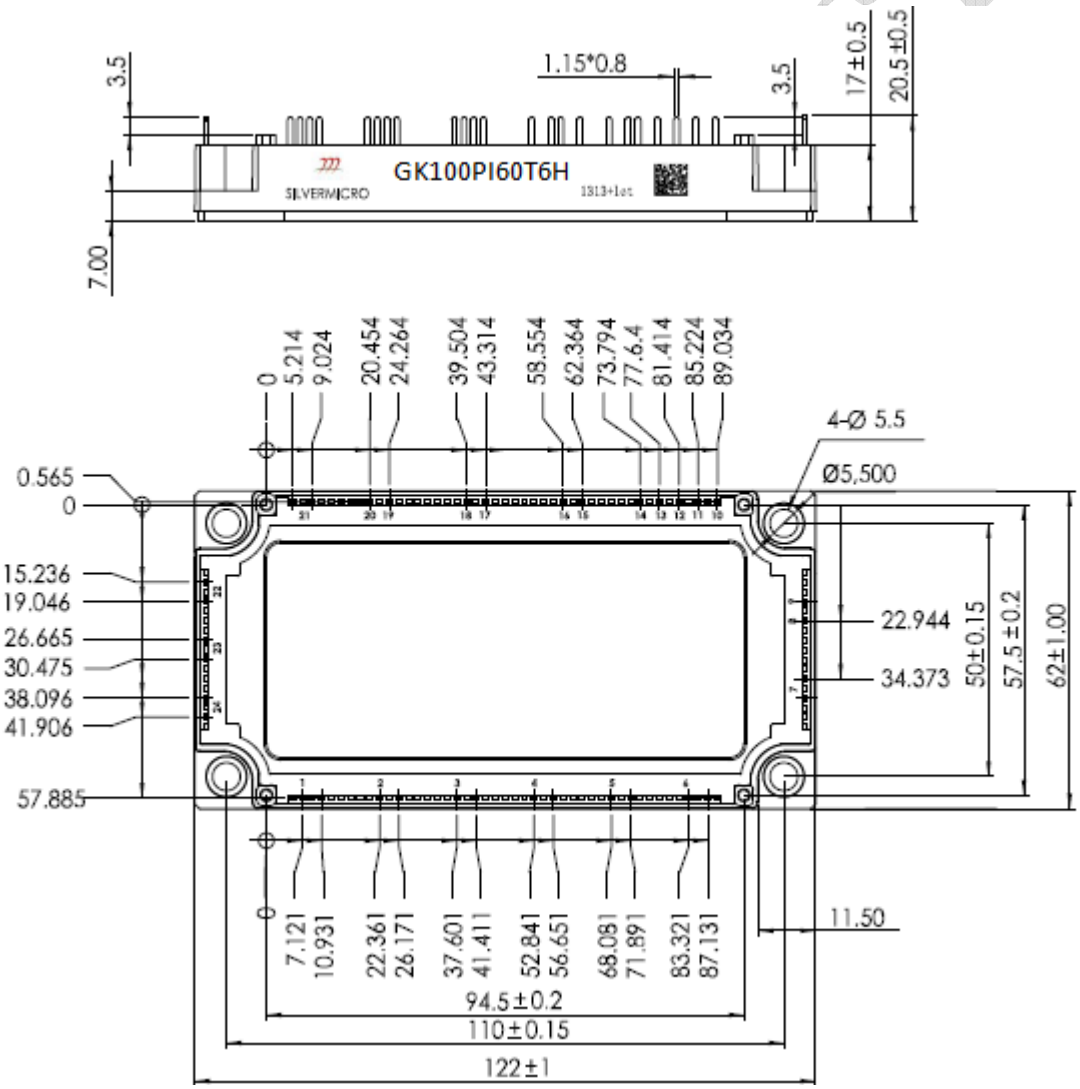


Fig.14 Reverse Bias Safe Operation Area (RBSOA)

Internal Circuit:



Package Outline (Unit: mm):



Announcement

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